

**AMENDMENTS TO THE CLAIMS**

1. (Original) A cleaner that is an aqueous solution containing phosphoric acid, hydrofluoric acid, and ammonia and/or amine and having a pH ranging from 2 to 12, wherein said aqueous solution contains:

0.5 to 25 mass% of phosphoric acid,

0.1 to 10 mass% of ammonia and/or amine, and

$5 \times 10^{-3}$  to 5.0 mass% of hydrofluoric acid.

2. (Original) The cleaner according to claim 2, wherein the pH is regulated by phosphoric acid.

3. (Original) The cleaner according to claim 1 or 2, which further includes a surface active agent and/or a chelate agent.

4. (Currently amended) The clearer according to ~~any one of claims 1 to 3~~ claim 1, which further includes hydrogen peroxide.

5. (Currently amended) The cleaner according to ~~any one of claims 1 to 4~~ claim 1, which is used for cleaning off particles and/or metal impurities out of the surface of a semiconductor device substrate.

6. (New) The clearer according to claim 2, which further includes hydrogen peroxide.

7. (New) The clearer according to claim 3, which further includes hydrogen peroxide.

8. (New) The cleaner according to claim 2, which is used for cleaning off particles and/or metal impurities out of the surface of a semiconductor device substrate.

.     9.     (New) The cleaner according to claim 3, which is used for cleaning off particles  
and/or metal impurities out of the surface of a semiconductor device substrate.

.     10.    (New) The cleaner according to claim 4, which is used for cleaning off particles  
and/or metal impurities out of the surface of a semiconductor device substrate.